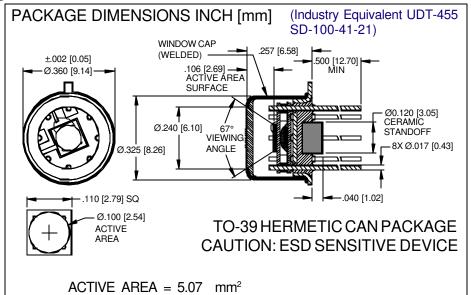
PHOTONIC DETECTORS INC.

Detector Amplifier Hybrid, Blue Enhanced (ref PDB-C705) Type PDB-705





RESPONSIVITY (A/W)

FEATURES

- Low input bias current
- Low offset voltage
- 1 MHz bandwidth

DESCRIPTION

The **PDB-705** is a low noise, medium speed, blue enhanced silicon photodiode integrated with a low noise JFET monolithic transimpedance op-amp. The feedback capacitor & resistor circuit are externally connected.

APPLICATIONS

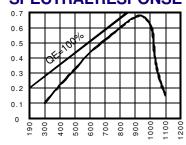
- Medical diagnostic
- Low signal level applications
- Spectroscopy

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS
VBR	Reverse Voltage		15	V
T _{STG}	Storage Temperature	-55	+125	∘C
То	Operating Temperature Range	0	+70	∘C
Ts	Soldering Temperature*		+240	∘C
I	Light Current		500	mA

^{*1/16} inch from case for 3 secs max

SPECTRAL RESPONSE



WAVELENGTH(nm)

PHOTODIODE ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Isc	Short Circuit Current	H = 100 fc, 2850 K	45	65		μA
ΙD	Dark Current	$H = 0, V_R = 10 V$		1.0	5.0	nA
RsH	Shunt Resistance	$H = 0, V_R = 10 \text{ mV}$.5	2		GΩ
TC Rsh	RSH Temp. Coefficient	$H = 0, V_R = 10 \text{ mV}$		-8		%/℃
C₁	Junction Capacitance	$H = 0, V_R = 10 V^{**}$		15		рF
λrange	Spectral Application Range	Spot Scan	350		1100	nm
λр	Spectral Response - Peak	Spot Scan		950		nm
V _{BR}	Breakdown Voltage	I = 10 µ A	100	125		V
NEP	Noise Equivalent Power	VR = 10 V @ Peak		2.5x10 ⁻¹⁴		W/ √ Hz
tr	Response Time	$RL = 1 K\Omega V_R = 10 V$		15		nS

Detector Amplifier Hybrid, Blue Enhanced (ref PDB-C705) Type PDB-705

AMPLIFIER SPECIFICATION TA = 25° C and VS = ± 15 vdc UNLESS OTHERWISE NOTED

CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
INPUT OFFSET VOLTAGE (Vos)	INITIAL OFFSET		0.75	2.0	mV
	LONGTERMOFFSETSTABILITY		15		μV/MONTH
AVERAGE INPUT OFFSET DRIFT (TCVos)	$R_L = 100 \text{ K}\Omega$			20	μV/°C
INPUT BIAS CURRENT (I₃)	OFFSET CURRENT, VCM=0		5	10	рА
INPUTOFFSET CURRENT (I∞)			5		рА
INPUT VOLTAGE RANGE (Iva)	COMMONMODE REJECTION VCM±10 V	±11	±12		V
INPUTVOLTAGENOISE	VOLTAGE 0, f=100 Hz		40		nV∕√Hz
	VOLTAGE 0, f=1 Khz		30		nV∕√Hz
INPUTCURRENTNOISE (in)	TYP f=100 Hz		1.8		fA/√Hz
FREQUENCYRESPONSE	UNITY GAIN, SMALL SIGNAL	0.8	1.0		MHz
	SLEW RATE, UNITY GAIN	1.0	1.8		V/µs
CLOSED LOOP GAIN (CLBW)	AVCL=+5 V		9		Mhz
SUPPLYCURRENT(Isr)					mP
SHORT CIRCUIT CURRENT			15		mA
POWERSUPPLY	OPERATING VOLTAGE	±4.5		±18	V

AMPLIFIER ABSOLUTE MAXIMUM RATING (TA=25°C UNLESS OTHERWISE NOTED)

AWI EII IET ABOOLOTE WAXWOOM HATING (TA-ES O GNEEDS OTHERWISE NOTES)					
PARAMETER	MIN	MAX	UNITS		
SUPPLYVOLTAGE		18	V		
DIFFERENTIAL INPUT VOLTAGE		±20	V		
STORAGETEMPERATURE	-55	+125	° C		
OPERATINGTEMPERATURE	0	+70	° C		

PIN CONNECTIONS

1- OFFSET ADJUSTMENT
2- INVERTING INPUT/ CATHODE OF PHOTODIODE

PHOTODIODE
3 - NON-INVERTING INPUT/ CASE
GROUND
4 - NEGATIVE SUPPLY VOLTAGE
5 OFFSET ADJUSTMENT
6 OUTPUT
7 - POSITIVE SUPPLY VOLTAGE
8 - ANODE OF PHOTODIODE

POWER SUPPLY RATED @ ±15 V RANGE ±4.3 V - ±18 V QUIESCENT CURRENT 200 µA MAX Ø.230 [5.84] PIN CIRCLE

BOTTOM VIEW

PHOTOVOLTAIC 5.1 mm ² Ø 2.5 mm PHOTODIODE PIN 8 250 KOhm PHOTOCONDUCTIVE